Amendments to the Specification

Please replace the paragraph beginning on page 11, line 32 with the following amended paragraph:

As indicated by the asteroid characteristic curve, it is possible to lower a magnetic threshold necessary to change the magnetic direction along the easy axis by applying a magnetic filed in the hard axis to free magnetic layer VL. In the case where operation points when the data is written are designed as in the example of Fig. 4, the data write magnetic field [[filed]] in the easy axis direction is designed to have an intensity H_{WR} in data write target tunneling magneto-resistance element TMR. That is, the value of the data write current carried to either bit line BL or digit line DL is designed so as to obtain data write magnetic field H_{WR}. Generally, data write magnetic field H_{WR} is given by the sum of a switching magnetic field H_{SW} necessary to switching of the magnetic direction and a margin ΔH. In other words, data write magnetic field H_{WR} is given by the formula: $H_{WR} = H_{SW} + \Delta H$.